



CHENMKO ENTERPRISE CO.,LTD

Halogens free devices

SURFACE MOUNT

Dual Digital Silicon Transistor

VOLTAGE 50 Volts CURRENT 100 mAmpere

CHUMA1GP

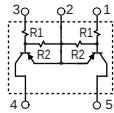
APPLICATION

* Switching circuit, Inverter, Interface circuit, Driver circuit.

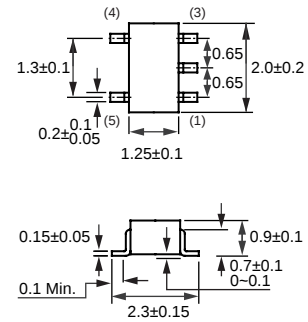
FEATURE

- * Small surface mounting type. (SC-88A/SOT-353)
- * High current gain.
- * Suitable for high packing density.
- * Low collector-emitter saturation.
- * High saturation current capability.
- * tow CHDTA124E chips in apackage.
- * Built in bias resistor(R1=22kΩ, Typ.)

CIRCUIT



SC-88A/SOT353



Dimensions in millimeters

SC-88A/SOT353

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	Supply voltage		—	-50	V
V _{IN}	Input voltage		-40	+10	V
I _O	DC Output current		—	-100	mA
P _{TOT}	Total power dissipation	T _{amb} ≤ 25 °C, Note 1	—	150	mW
T _{STG}	Storage temperature		-55	+150	°C
T _J	Junction temperature		—	150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

RATING CHARACTERISTIC (CHUMA1GP)

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{I(off)}	Input off voltage	I _O =-100uA; V _{CC} =-5.0V	-0.5	—	—	V
V _{I(on)}	Input on voltage	I _O =-5mA; V _O =-0.2V	—	—	-3.0	V
V _{O(on)}	Output voltage	I _O =-10mA; I _I =-0.5mA	—	-0.1	-0.3	V
I _I	Input current	V _I =-5V	—	—	-0.36	mA
I _{C(off)}	Output current	V _I =0V; V _{CC} =-50V	—	—	-0.5	uA
h _{FE}	DC current gain	I _O =-5mA; V _O =-5.0V	56	—	—	
R ₁	Input resistor		15.4	22.0	28.6	KΩ
R ₂ /R ₁	Resistor ratio		0.8	1.0	1.2	

Note

1.Pulse test: t_p≤300uS; δ≤0.02.

RATING CHARACTERISTIC CURVES (CHUMA1GP)

Typical Electrical Characteristics

Fig.1 Input voltage vs. output current (ON characteristics)

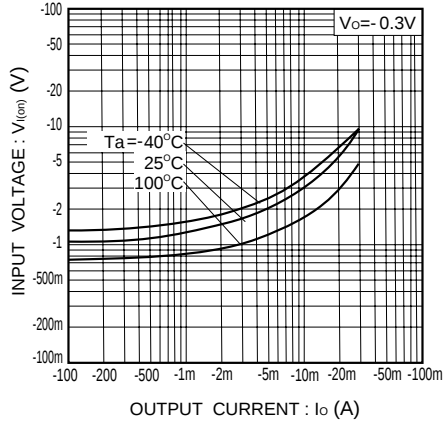


Fig.2 Output current vs. input voltage (OFF characteristics)

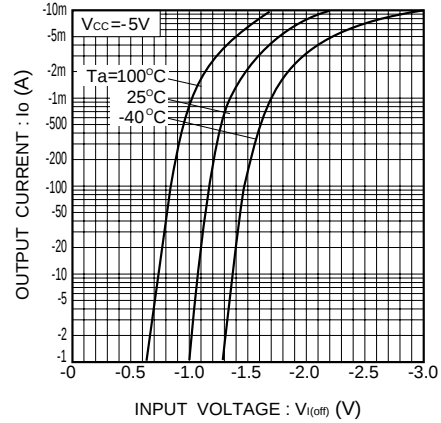


Fig.3 DC current gain vs. output current

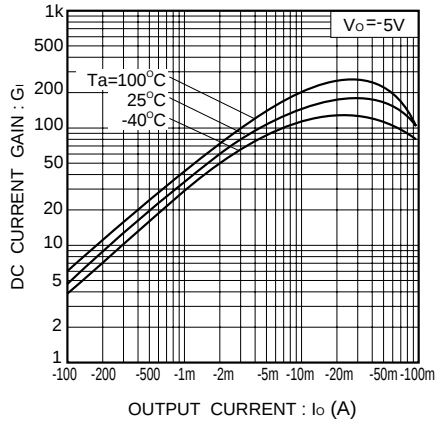


Fig.4 Output voltage vs. output current

